



## SOT-23-3L DIGITAL TRANSISTORS TRANSISTORS(PNP)

## **FEATURES**

- \* Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors.(see equivalent circuit).
- \* The bias resistors consist of thin-film resistors with complete isolation to allow negative biasing of the input. They also have the advantage of almost completely Eliminating parasitic effects.
- \* Only the on/off conditions need to be set for operation marking device design easy.

## **MECHANICAL DATA**

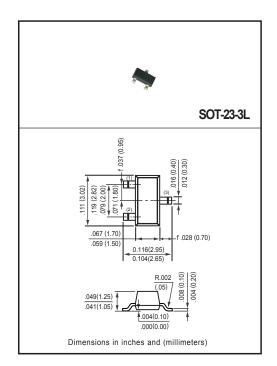
- \* Case: Molded plastic
- \* Epoxy: UL 94V-O rate flame retardant
- \* Lead: MIL-STD-202E method 208C guaranteed
- \* Mounting position: Any \* Weight: 0.009 gram

## MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.



(1)BASE (2)EMITTER (3)COLLECTOR



#### MAXIMUM RATINGES ( @ TA = 25°C unless otherwise noted )

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RATINGS	SYMBOL	VALUE	UNITS				
Collector-base voltage	V <sub>(BR)CBO</sub>	-50	V				
Collector-emitter voltage	V <sub>(BR)CEO</sub>	-50	V				
Emitter-base voltage	V <sub>(BR)EBO</sub>	-5	V				
Collector current	Ic	-100	mA				
Collector power dissipation	Pc	200	mW				
Junction temperature	Tj	150	°C				
Storage temperature	T <sub>stg</sub>	-55~150	°C				

#### ELECTRICAL CHARACTERISTICS ( @ TA = 25°C unless otherwise noted )

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CHARACTERISTICS	SYMBOL	MIN.	TYP.	MAX.	UNITS
Collector-base breakdown voltage (I <sub>C</sub> = -50μA)	V <sub>(BR)CBO</sub>	-50	-	-	V
Collector-emitter breakdown voltage (I <sub>C</sub> = -1mA)	V <sub>(BR)CEO</sub>	-50	-	-	V
Emitter-base breakdown voltage (I <sub>E</sub> = -50μA)	V <sub>(BR)EBO</sub>	-5	-	-	٧
Collector cut-off current (V <sub>CB</sub> = -50V)	Ісво	-	-	-0.5	μА
Emitter cut-off current (V <sub>EB</sub> = -4V)	IEBO	-	-	-0.5	μА
Collector-emitter saturation voltage (I <sub>C</sub> = -5mA,I <sub>B</sub> = -0.25mA)	V <sub>CE(sat)</sub>	-	-	-0.3	V
DC current transfer ratio (V <sub>CE</sub> = -5V,I <sub>C</sub> = -1mA)	h <sub>FE</sub>	100	-	600	-
Transistion frequency (V <sub>CE</sub> = -10V, I <sub>E</sub> = 5mA, f=100MHz)	f <sub>T</sub>	-	250	-	MHz
Input resistor	R <sub>1</sub>	3.29	4.7	6.11	ΚΩ

# **RATING AND CHARACTERISTICS CURVES (DTA143TKA)**

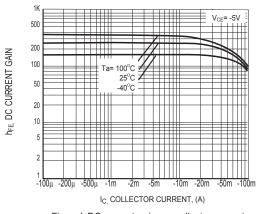


Figure1 DC current gain vs. collector current

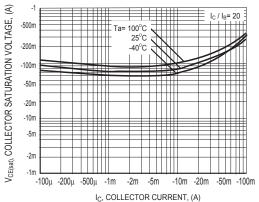


Figure2 Collector-emitter saturation voltage vs.collector current

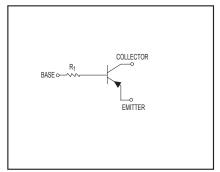


Figure3 Equivalent circuit

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